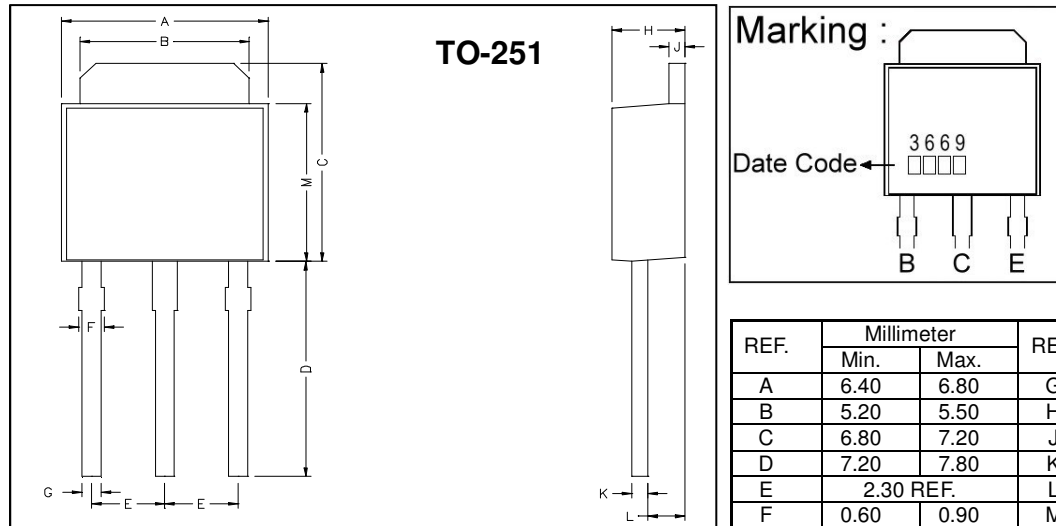


GI3669**NPN EPITAXIAL PLANAR TRANSISTOR****Description**

The GI3669 is designed for using in power amplifier applications, power switching applications.

Package Dimensions**Absolute Maximum Ratings (TA=25°C)**

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V _{CB0}	80	V
Collector to Emitter Voltage	V _{CEO}	80	V
Emitter to Base Voltage	V _{EB0}	5	V
Collector Current (DC)	I _C	2	A
Total Device Dissipation (TA=25°C)	P _D	1.25	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C

Electrical Characteristics (TA = 25°C unless otherwise noted)

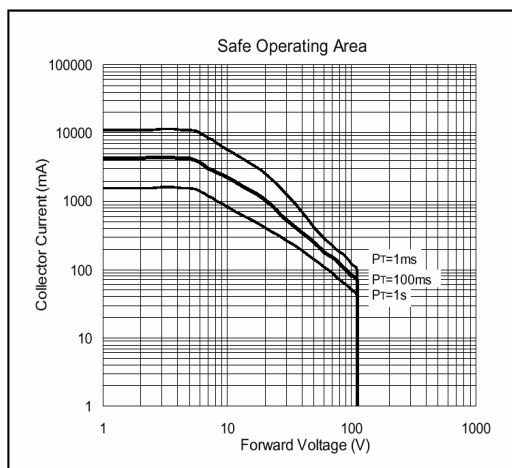
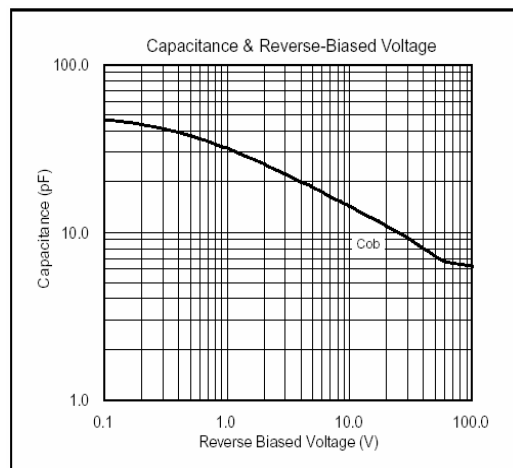
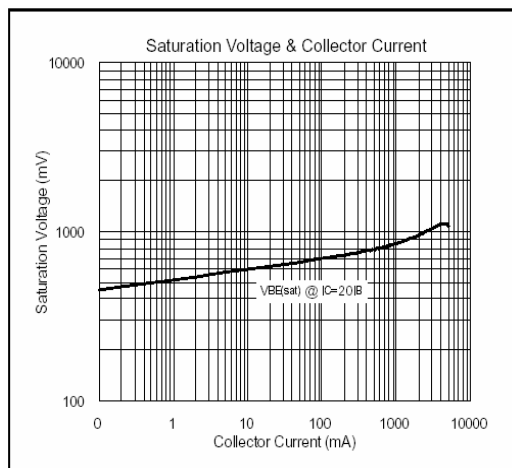
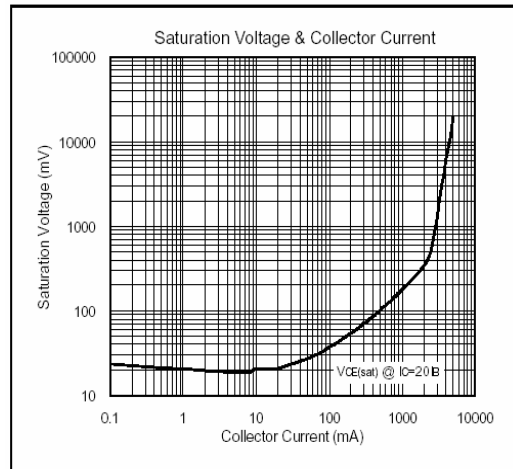
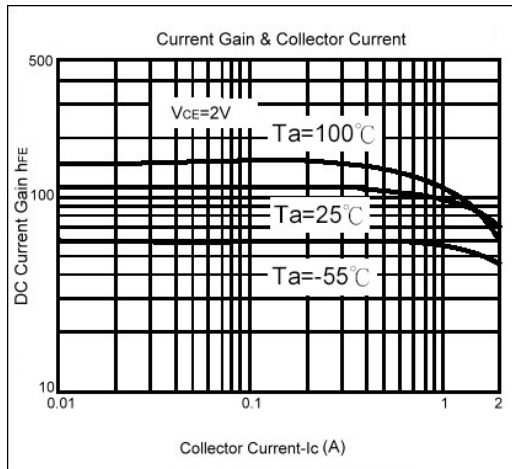
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CB0}	80	-	-	V	I _C =100uA, I _E =0
BV _{CEO}	80	-	-	V	I _C =10mA, I _B =0
BV _{EB0}	5	-	-	V	I _E =100uA, I _C =0
I _{CB0}	-	-	1	uA	V _{CB} =80V, I _E =0
I _{EB0}	-	-	1	uA	V _{EB} =5V, I _C =0
*V _{CE(sat)}	-	0.15	0.5	V	I _C =1A, I _B =50mA
*V _{BE(sat)}	-	0.9	1.2	V	I _C =1A, I _B =50mA
*h _{FE1}	70	-	240		V _{CE} =2V, I _C =0.5A
*h _{FE2}	40	-	-		V _{CE} =2V, I _C =1.5A
f _T	-	100	-	MHz	V _{CE} =2V, I _E =500mA, f=100MHz
C _{ob}	-	30	-	pF	V _{CB} =10V, I _E =0, f=1MHz
t _{on} (Turn-On Time)	-	0.2	-	us	V _{CC} =30V, R _L =30Ω,
t _{stg} (Storage Time)	-	1.0	-	us	I _C =1A,
t _f (Fall Time)	-	0.2	-	us	I _{B1} =-I _{B2} =50mA, Duty Cycle ≤ 1%

*Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Classification Of hFE1

Rank	O	Y
Range	70 ~ 140	120 ~ 240

Characteristics Curve

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